

## Transient Voltage Suppression Diodes Surface Mount – 6600W > SM8S series

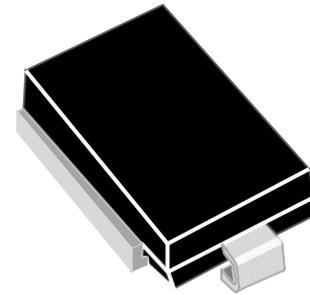
### Descriptions

Transient Voltage Suppressors (TVS) are semiconductor devices designed to provide protection against over voltage transients. When over voltage events occur, the silicon TVS activates from an very high impedance status to a very low impedance status by operating in the avalanche mode and uses a large junction area to absorb large transient currents in a fast response time, protecting voltage sensitive electronics equipment from damaging.

Boarden supplies unipolar and bipolar TVS devices with axial and SMD packages, with maximum working voltage 5V to 550V, maximum power dissipation from 200W-5000W.

### Features

- Glass passivated chip junction in DO-218AB Package
- Junction passivation optimized design passivated anisotropic rectifier technology
- $T_J = 175^{\circ}\text{C}$  capability suitable for high reliability and automotive requirement
- Available in uni-directional polarity only
- Low leakage current
- Low forward voltage drop
- High surge capability
- Meets ISO7637-2 surge specification (varied by test condition)
- Meets MSL level 1, per J-STD-020, LF maximum peak of  $245^{\circ}\text{C}$
- AEC-Q101 qualified
- RoHS compliant



**DO-218AB**

### Order Information

Device	Qty per Box	Tape
SM8SxxA	750	13" Reel

### Applications

Used in sensitive electronics protection against voltage transients induced by inductive load switching and lighting, especially for automotive load dump protection application.

### Maximum Ratings and Thermal Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Pulse Power Dissipation	$P_{PP}$	with 10/1000 $\mu\text{s}$ waveform	6600
		with 10/10000 $\mu\text{s}$ waveform	5200
Power dissipation on infinite heatsink at $T_C = 25^{\circ}\text{C}$	$P_D$	8.0	W
Peak pulse current with 10/1000 $\mu\text{s}$ waveform	$I_{PPM}^{(1)}$	See next table	A
Peak Forward Surge Current, 8.3ms Single Half Sine-Wave	$I_{FSM}$	700	A
Operating junction and Storage Temperature Range	$T_J, T_{STG}$	-55~175	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Lead	$R_{\theta JC}$	0.9	$^{\circ}\text{C}/\text{W}$

**Notes:**

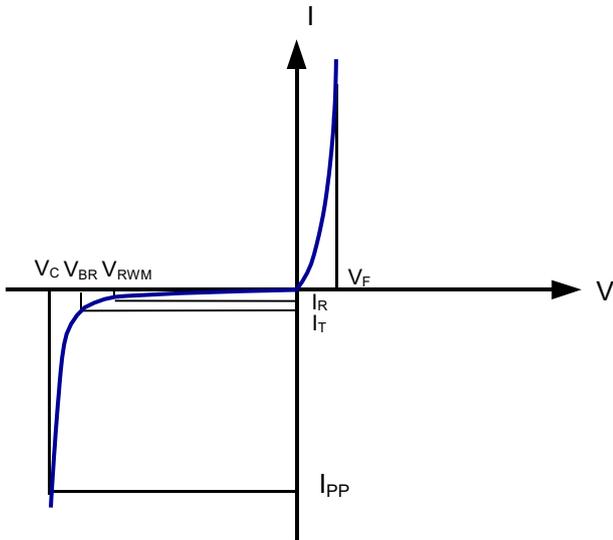
1) Non-repetitive current pulse derated above  $T_A = 25^{\circ}\text{C}$

**Electrical Characteristics (TA=25°C unless otherwise noted)**

Type Number	V <sub>RMW</sub>	I <sub>R</sub> @V <sub>RMW</sub>		V <sub>BR</sub> @I <sub>T</sub>		I <sub>T</sub>	V <sub>C</sub> @I <sub>PP</sub>	I <sub>PP</sub>
		(μA) @25°C	(μA) @T <sub>J</sub> =175°C	Min(V)	Max(V)			
SM8S10A	10.0	5	250	11.1	12.3	5	17.0	388
SM8S11A	11.0	5	150	12.2	13.5	5	18.2	363
SM8S12A	12.0	5	150	13.3	14.7	5	19.9	332
SM8S13A	13.0	5	150	14.4	15.9	5	21.5	307
SM8S14A	14.0	5	150	15.6	17.2	5	23.2	284
SM8S15A	15.0	5	150	16.7	18.5	5	24.4	270
SM8S16A	16.0	5	150	17.8	19.7	5	26.0	253
SM8S17A	17.0	5	150	18.9	20.9	5	27.6	239
SM8S18A	18.0	5	150	20.0	22.1	5	29.2	226
SM8S20A	20.0	5	150	22.2	24.5	5	32.4	204
SM8S22A	22.0	5	150	24.4	26.9	5	35.5	186
SM8S24A	24.0	5	150	26.7	29.5	5	38.9	170
SM8S26A	26.0	5	150	28.9	31.9	5	42.1	157
SM8S28A	28.0	5	150	31.1	34.4	5	45.4	145
SM8S30CA	30.0	5	150	33.3	36.8	5	48.4	136
SM8S32CA	32.0	5	150	35.5	39.4	5	51.4	128.5
SM8S33CA	33.0	5	150	36.7	40.6	5	53.3	124
SM8S36CA	36.0	5	150	40.0	44.2	5	58.1	114
SM8S40CA	40.0	5	150	44.4	49.1	5	64.5	102
SM8S43CA	43.0	5	150	47.8	52.8	5	69.4	95.1

For all types maximum V<sub>F</sub> = 1.8 V at I<sub>F</sub> = 100 A measured on 8.3 ms single half sine-wave or equivalent square wave, duty cycle = 4 pulses per minute maximum

**I-V Curve Characteristics**



Uni-Directional TVS

**VRWM - Reverse Stand-Off Voltage** - Working Peak Reverse Voltage

**VBR - Breakdown Voltage** - Maximum current that flows through the TVS at a specified test current ( $I_T$ )

**IT - Test Current** - Test Current

**VC - Clamping Voltage** - Peak voltage measured across the suppressor at a specified  $I_{ppm}$  (peak impulse current)

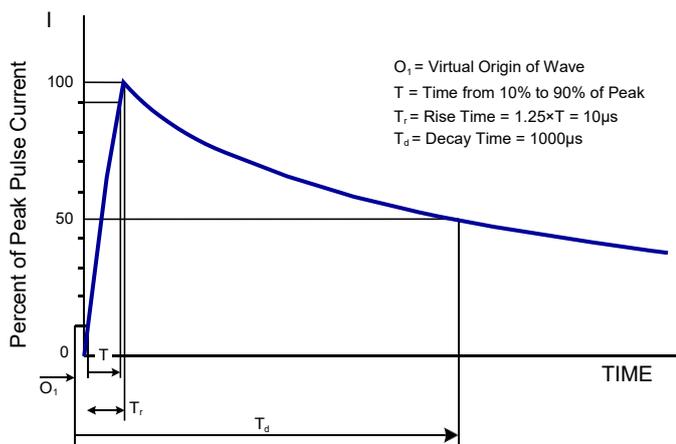
**IPP - Peak Pulse Current** - Maximum Reverse Peak Pulse Current

**PPP - Peak Pulse Power Dissipation** - Max power dissipation

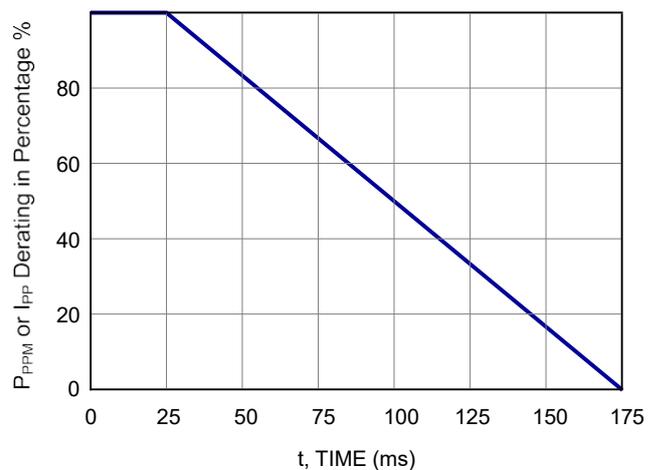
**IR - Reverse Leakage Current** - Current measured at  $V_{RWM}$

**VF - Forward Voltage** - Drop for Uni-directional

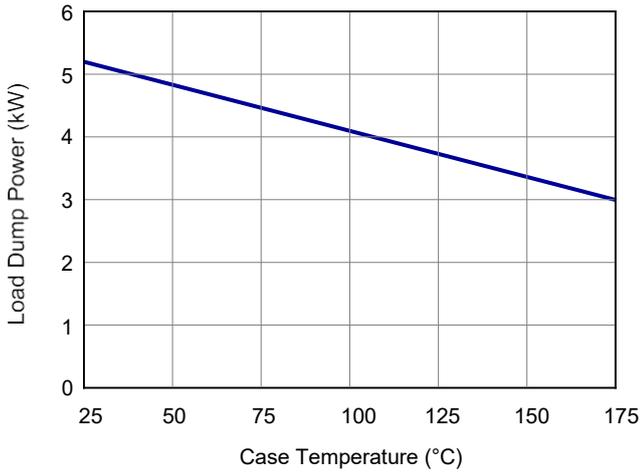
**Ratings and Characteristic Curves (TA=25°C unless otherwise noted)**



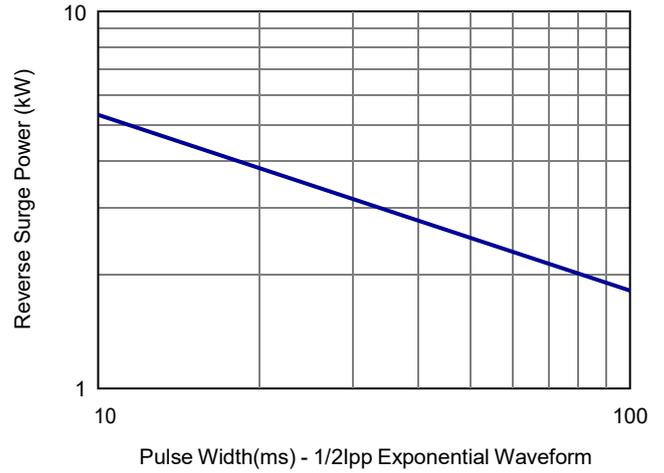
Pulse Waveform- 10/1000µs



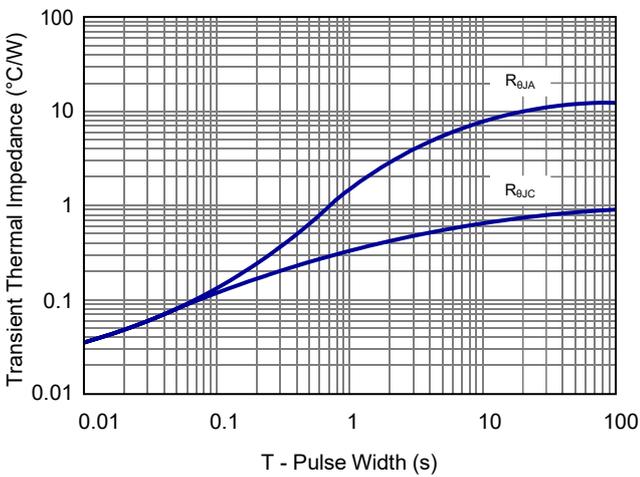
Pulse Derating Curve



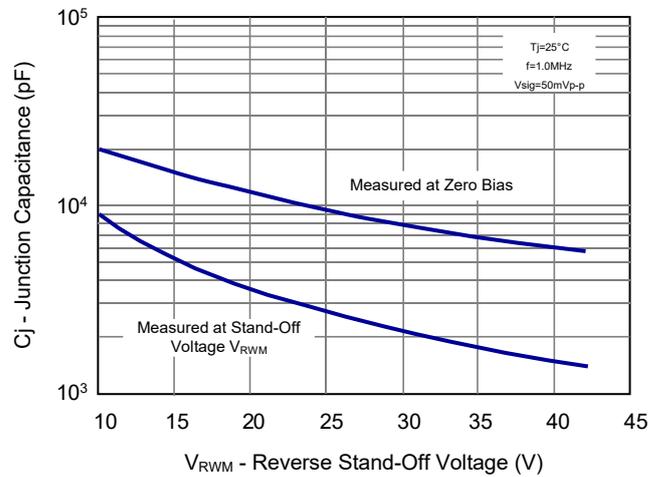
**Load Dump Power Characteristics**  
(10ms Exponential Waveform)



**Reverse Power Capability**



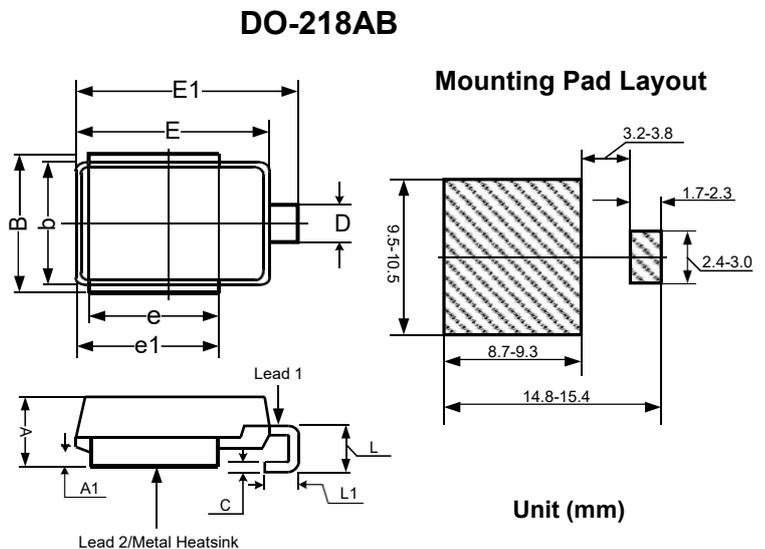
**Typical Transient Thermal Impedance**



**Typical Junction Capacitance**

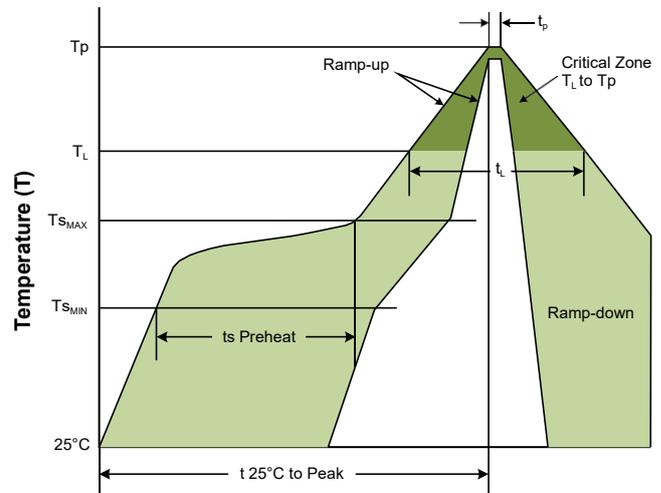
**Product Dimensions**

Dimensions	Inches		Millimeters	
	Min	Max	Min	Max
A	0.185	0.201	4.70	5.10
A1	0.016	-	0.40	-
B	0.374	0.413	9.50	10.50
b	0.327	0.342	8.30	8.70
C	0.020	0.028	0.50	0.70
D	0.094	0.118	2.40	3.00
E	0.524	0.539	13.30	13.70
E1	0.592	0.628	15.00	16.00
e	0.335	0.358	8.50	9.10
e1	0.374	0.398	9.50	10.10
L	0.106	0.146	2.70	3.70
L1	0.059	0.098	1.50	2.50



## Soldering Parameters

Profile Feature	Lead-Free Assembly
Average Ramp-up Rate ( $T_{S_{MAX}}$ to $T_p$ ) Average Ramp-down Rate ( $T_p$ to $T_L$ )	3°C/second max. 6°C/second max.
<b>Preheat</b> • Temperature Min ( $T_{S_{MIN}}$ ) • Temperature Max ( $T_{S_{MAX}}$ ) • Time ( $t_s$ Preheat)	150°C 200°C 60-180 seconds
<b>Time maintained above:</b> • Temperature ( $T_L$ ) • Time ( $t_L$ )	217°C 60-150 seconds
<b>Peak/Classification Temperature</b> • Temperature ( $T_p$ )	260 <sup>+0/-5</sup> °C
<b>Time within 5°C of actual Peak</b> Time ( $t_p$ )	20-40 seconds
<b>Time 25°C to peak Temperature</b>	8 minutes max
<b>Do not exceed</b>	280 °C



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